

SLA50000H Series

High Density Gate Array

- Ultra-high-speed, high density and low power consumption
- Low voltage operation: 3.3V and 2.0V
- Number of raw gates: 28,710 to 815,468 gates

■ DESCRIPTION

The SLA50000H Series are high-speed, high-density and powerful drive gate arrays using SOG type CMOS 0.35µm processes. For this Series, we have prepared a product line up of gate arrays ranging from 28,710 through 815,468 of raw gates for immediate applications to large-scale and high-speed systems.

To conform to many application fields with low voltage operation, these gate arrays are compatibly usable for 3V systems and 2V systems. Furthermore, we have prepared low noise output cells of " μA " orders for wide range of applications including miniature portable equipment.

■ FEATURES

- Super-high density (adopting 0.35μm silicon gate CMOS with 2-, 3- and 4-metal layers)
- High-speed operation (operation delay of internal gate = 0.140ns at 3.3V, 2-input power NAND standard)
- Internal gate = 3.3 and 2.0V, I/O buffer = 5.0, 3.3 and 2.0V (built-in level shifter)
- Low power consumption (0.70μW/MHz/BC when internal cell = 3.3V)
- Output drivability (IoL = 0.1, 1, 3, 8, 12, 24mA when PCI = 5.0V, IoL = 0.1, 1, 2, 6, 12mA when PCI = 3.3V, IoL = 0.05, 0.3, 0.6, 2, 4mA when 2.0V)
- RAM, PLL*, IrDA* and various function cells available
- Low noise output cell, PCI I/F, USB I/F*, Fail-Safe output, JTAG

■ PRODUCT LINEUP

| Master | 2-layer Metal | SLA5028H | SLA5075H | SLA5099 | SLA5125H | SLA5177H | SLA5250H | SLA5335H | SLA5442H | SLA5506H | SLA5668H | SLA5815H |
|---|----------------|---|--------------|--------------|--------------|--------------|--------------|--------------|--------------|--------------|--------------|--------------|
| | 3-layer Metal | SLA502TH | SLA507TH | SLA509T | SLA512TH | SLA517TH | SLA525TH | SLA533TH | SLA544TH | SLA550TH | SLA566TH | SLA581TH |
| Features | 4-layer Metal | SLA502QH | SLA507QH | SLA509Q | SLA512QH | SLA517QH | SLA525QH | SLA533QH | SLA544QH | SLA550QH | SLA566QH | SLA581QH |
| Total BCs (Raw Gates) | | 28,710 | 75,774 | 99,198 | 125,772 | 177,062 | 250,160 | 335,858 | 442,112 | 506,688 | 668,552 | 815,468 |
| _ | 2-layer Metal | 14,355 | 35,613 | 46,623 | 56,597 | 79,677 | 112,572 | 144,418 | 176,844 | 202,675 | 267,420 | 326,187 |
| Usable BCs | 3-layer Metal | 25,264 | 64,407 | 84,318 | 100,617 | 132,796 | 187,620 | 251,893 | 309,478 | 354,681 | 467,986 | 570,827 |
| | 4-layer Metal | 27,274 | 71,985 | 94,238 | 119,483 | 168,208 | 237,652 | 319,065 | 397,900 | 456,019 | 601,696 | 733,921 |
| Number of PADs (In Case of Micro Pitch)* | | 88 (104) | 144 (168) | 168 (192) | 188 (216) | 224 (256) | 264 (304) | 308 (352) | 352 (404) | 376 (432) | 432 (496) | 480 (548) |
| Propagation Delay | Internal Gates | tpd = 0.140ns (standard at 3.3V), 0.21ns (standard at 2.0V) | | | | | | | | | | |
| | Input Buffers | tpd = 0.38ns (standard at 5.0V) level shifter, 0.4ns (standard at 3.3V), 1.3ns (standard at 2.0V) | | | | | | | | | | |
| | Output Buffers | tpd = 2.12ns (standard at 5.0V) level shifter, 2.02ns (standard at 3.3V), 3.9ns (standard at 2.0V), CL = 15pF | | | | | | | | | | |
| I/O Level | | CMOS, LVTTL, PCI, USB* | | | | | | | | | | |
| Input Mode | | LVTTL, CMOS, Pull-up/Pull-down, Schmitt, 2.0/3.3V Level interface (Level shifter) | | | | | | | | | | |
| Output Mode | | Normal, Open drain, 3-state, Bi-directional, 2.0/3.3V Level interface (Level shifter) | | | | | | | | | | |